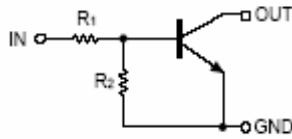


PNP Transistors

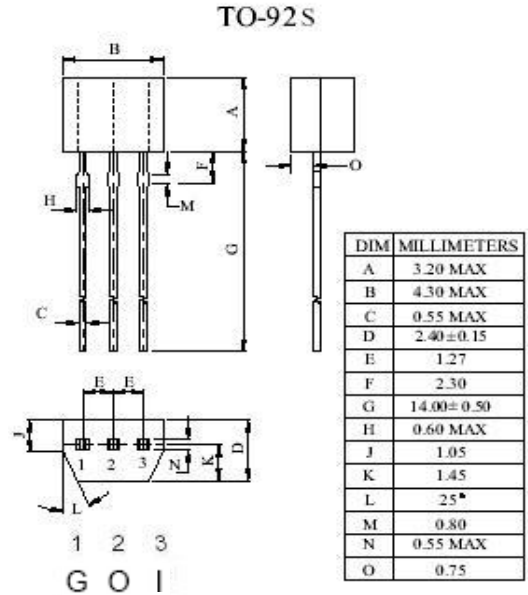
—NPN Silicon—

■■ **APPLICATION:** Interface Circuit and Driver Circuit Applications.



■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-40~10	V
Output Current	I_O	-30	mA
	$I_{C(Max.)}$	-100	mA
Power Dissipation	P_d	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Input Voltage	$V_{I(off)}$			-0.5	V	$V_{CC}=-5V I_O=-100\mu A$
	$V_{I(on)}$	-3			V	$V_{CC}=-0.2V I_O=-5mA$
Output Voltage	$V_{O(on)}$		-0.1	-0.3	V	$I_O=-10mA I_I=-0.5mA$
Input Current	I_I			-0.36	mA	$V_I=-5V$
Output Current	$I_{O(off)}$			-0.5	uA	$V_{CC}=-50V V_I=0V$
DC Current Gain	G_I	56				$V_O=-5V I_O=-5mA$
Input Resistance	R_1	15.4	22	28.6	KΩ	
Input Resistance	R_2	15.4	22	28.6	KΩ	
Gain bandwidth product	f_T		250		MHz	$V_{CE}=-10V I_E=5mA f=100MHz$

■■ **G_I Classification And Marking**

Mark	A124ES
Classification	
G_I	≥56